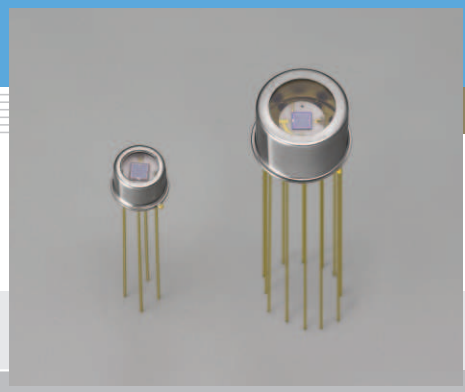


Two-color detector

K1713/K3413-01, -02

Broad spectral response range from UV through IR



K1713/K3413-01, -02 detectors have a sandwich structure in which an infrared transmitting silicon photodiode is mounted over an infrared detector element. This structure allows you to design instruments using the same optical path from UV through IR.

Features

- Broad spectral response
Suitable for spectrophotometers, flame monitors, etc.
- Noncooled type:
Room temperature operation for easy handling
One-stage thermoelectrically cooled type:
Keeps the detector temperature at a constant level to make high-precision measurements.

Applications

- Spectrophotometers
- Laser monitors
- Flame monitors
- Radiation thermometers

Accessories (Optional)

- Heatsink for thermoelectrically cooled type A3179-03
- Temperature controller for thermoelectrically cooled type C1103-04
- Photosensor amplifier C9329
- Amplifier for PbS and PbSe detectors C3757-02

General ratings / Absolute maximum ratings

Type No.	Dimensional outline/ Window material *1	Package	Cooling	Detector	Active area size (mm)	Absolute maximum ratings				
						Thermistor allowable dissipation (mW)	TE-cooler allowable current (A)	Reverse voltage VR (V)	Operating temperature T _{opr} (°C)	Storage temperature T _{stg} (°C)
K1713-01	①/S	TO-5	Non-cooled	Si	2.4 × 2.4	-	-	5	-30 to +50	-55 to +50
				PbS	1.8 × 1.8			100 *2		
K1713-02				Si	2.4 × 2.4			5		
				PbSe	1.8 × 1.8			100 *2		
K3413-01	②/S	TO-8	One-stage TE-cooled	Si	2.4 × 2.4	0.2	1.5	5	-30 to +50	-55 to +50
				PbS	1.8 × 1.8			100 *2		
				Si	2.4 × 2.4			5		
K3413-02				PbSe	1.8 × 1.8			100 *2		

Electrical and optical characteristics (Typ., unless otherwise noted)

Type No.	Detector	Measurement condition	Peak sensitivity wavelength λ_p (μm)	Photo sensitivity S $\lambda = \lambda_p$ (A/W)	Shunt resistance or dark resistance (M Ω)	D* $\lambda = \lambda_p$ (cm · Hz ^{1/2} /W)	Rise time tr VR=0 V RL=1 k Ω 10 to 90 % (μs)
		Element temperature T (°C)					
K1713-01	Si	25	0.94	0.45	300	1.4×10^{13}	0.2 *4
	PbS		2.2	6×10^4 (V/W)	0.2 to 2	$5 \times 10^{10} *3$	200 Max. *5
K1713-02	Si	25	0.94	0.45	300	1.4×10^{13}	0.2 *4
	PbSe		4.0	5×10^2 (V/W)	0.5 to 1.8	$5 \times 10^8 *3$	3 Max. *5
K3413-01	Si	25	0.94	0.45	300	1.4×10^{13}	0.2 *4
	PbS	-10	2.4	3×10^5 (V/W)	0.5 to 10	$1 \times 10^{11} *3$	600 Max. *5
K3413-02	Si	25	0.94	0.45	300	1.4×10^{13}	0.2 *4
	PbSe	-10	4.1	1.5×10^3 (V/W)	1.5 to 5	$1 \times 10^9 *3$	5 Max. *5

*1: Window material S: sapphire glass

*2: Maximum supply voltage

*3: Light source 500 K black body
Chopping frequency: 600 Hz,
Noise bandwidth: 60 Hz

*4: $\lambda = 655$ nm

*5: 0 to 63 %

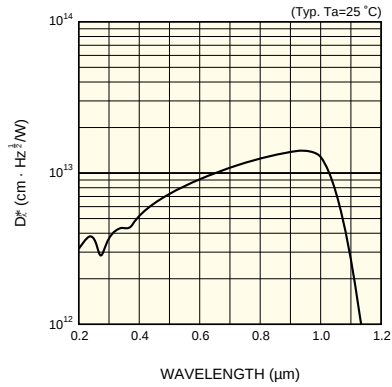
Supply voltage: 15 V

Load resistance: nearly equal to element dark resistance

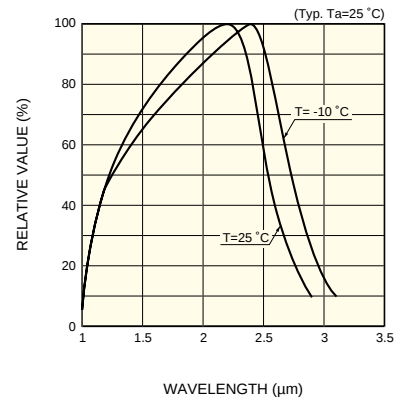
Input energy: 4.8 $\mu\text{W}/\text{cm}^2$ (PbSe: 16.7 $\mu\text{W}/\text{cm}^2$)

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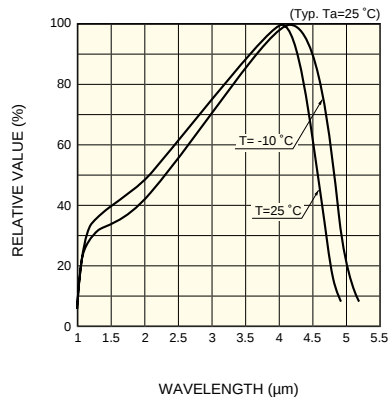
■ Spectral response

Si photodiode


KIRDB0058EE

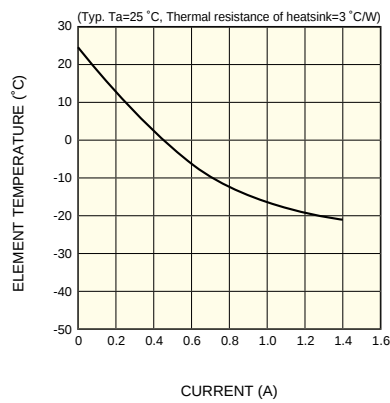
PbS photoconductive detector


KIRDB0282EA

PbSe photoconductive detector


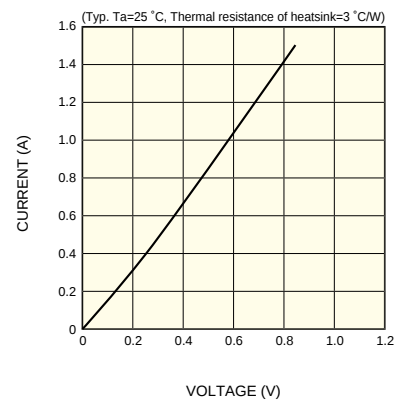
KIRDB0283EA

■ Cooling characteristics of TE-cooler



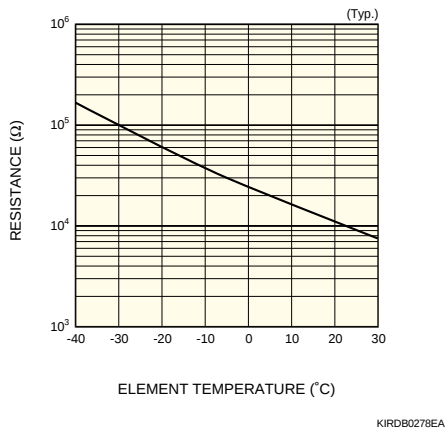
KIRDB0276EA

■ Current vs. voltage characteristics of TE-cooler



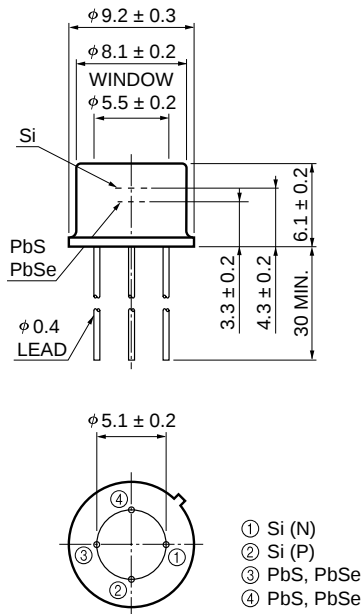
KIRDB0277EA

Thermistor temperature characteristic



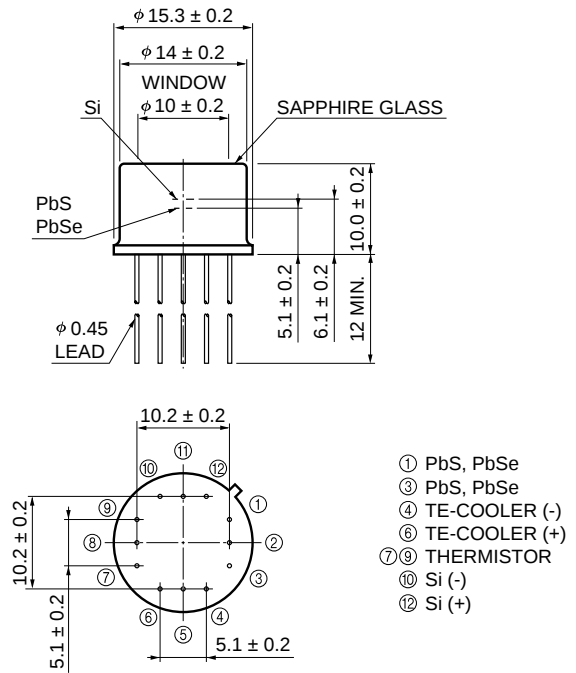
Dimensional outline (unit: mm)

① K1713-01, -02



KIRDA0041EE

② K3413-01, -02



KIRDA0043EE

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, www.hamamatsu.com

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741

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